


IN THE ABSTRACT:

Please amend the following paragraph starting at page 143, line 2 as follows:

The ~~present~~ invention provides a semiconductor element ~~comprising~~ having a semiconductor junction composed of silicon-based films, ~~the element being characterized in that at least one of the silicon-based films contains~~ containing a microcrystal, and microcrystal. The microcrystal is located in at least one interface region of the silicon-based ~~films~~ film containing the microcrystal and has no orientation property. Further, the ~~present~~ invention provides a semiconductor element ~~comprising~~ having a semiconductor junction composed of silicon-based films, ~~wherein at least one of the silicon-based films contains~~ containing a microcrystal, and the orientation property of the microcrystal ~~in the silicon-based film containing the microcrystal changes~~ changing in a film thickness direction of the silicon-based film containing the microcrystal. ~~In order to provide an inexpensive silicon-based film showing excellent performance, the present invention provides a~~ Thereby, a silicon-based film having a shortened tact time, an increased film forming rate, and excellent characteristics, and a semiconductor element including this silicon-based film, ~~and a semiconductor element using this silicon-based film and having excellent adhesion and environmental resistance~~ can be obtained.